

## 1. General description

WMS30N050S is a high performance logic level N-channel MOSFET in TO252 package, which utilizes advanced Trench MOSFET technology to provide low  $R_{DS(on)}$  and gate charge. It is designed and qualified in a wide range of industrial and consumer applications.



## 2. Features and benefits

- Advance High Cell Density Trench Technology
- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low Capacitance to Minimize Switching Losses
- Optimized Gate Charge to Minimize Driver Losses
- 100% UIS Tested
- RoHS Compliant and Halogen Free

## 3. Applications

- DC-DC Converters
- BLDC Motor Control
- Load Switch
- Lithium-ion Battery Protection

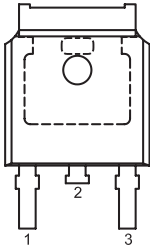
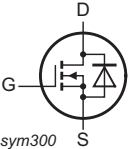
## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
<b>Absolute maximum rating</b>							
$V_{DS}$	drain-source voltage			30			V
$V_{GS}$	gate-source voltage			±20			V
$I_D$	continuous drain current	$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C}$	[1]	87			A
$P_{tot}$	power dissipation	$T_{mb} = 25\text{ °C}$		63			W
$T_j$	junction temperature			-55 to 150			°C
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
<b>Static characteristics</b>							
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		-	4.1	5.0	mΩ
		$V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$		-	5.8	8.0	mΩ
<b>Dynamic characteristics</b>							
$Q_{G(tot)}$	total gate charge	$I_D = 20\text{ A}; V_{DS} = 15\text{ V}; V_{GS} = 10\text{ V}$		-	44	-	nC

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WMS30N050S	TO252	WMS30N050SJ	Reel	2500	TO252N	14-Nov-2016

## 7. Marking

Table 4. Marking codes

Type number	Marking codes
WMS30N050S	WMS 30N050

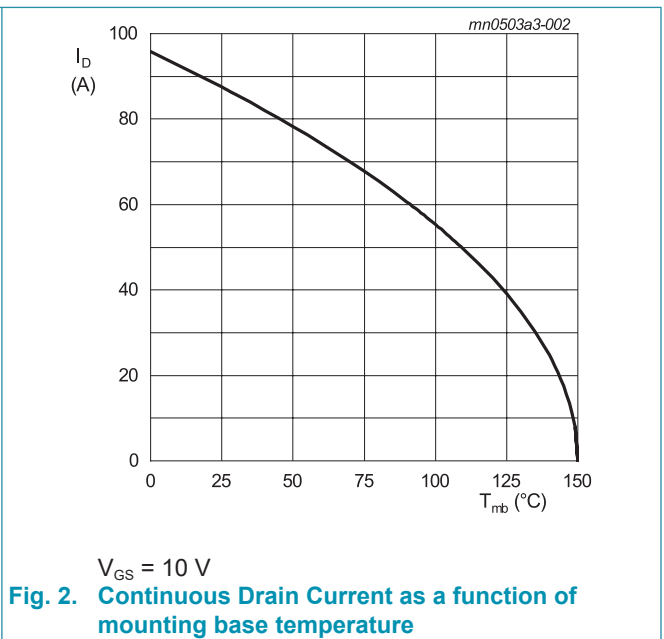
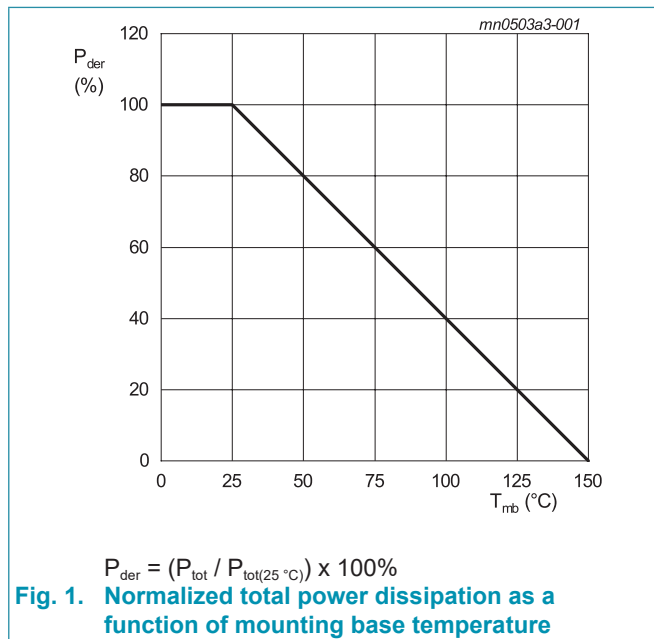
## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{DS}$	drain-source voltage			30	V
$V_{GS}$	gate-source voltage			±20	V
$I_D$	continuous drain current	$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C}$	[1]	87	A
		$V_{GS} = 10\text{ V}; T_{mb} = 120\text{ °C}$		43	A
$I_{DM}$	pulsed drain current	$t_p = 10\text{ }\mu\text{s}; T_{mb} = 25\text{ °C}$		348	A
$P_{tot}$	power dissipation	$T_{mb} = 25\text{ °C}$		63	W
$E_{as}$	single pulse drain-to-source avalanche	$I_{AS} = 28\text{ A}; L = 0.1\text{ mH}; R_{GS} = 25\text{ }\Omega;$ $V_{GS} = 10\text{ V}; T_j = 25\text{ °C}$		39	mJ
$T_{stg}$	storage temperature			-55 to 150	°C
$T_j$	junction temperature			-55 to 150	°C

[1] Calculated continuous current based on maximum allowable junction temperature. Package current limitation is 50A.



### 9. Thermal & Mechanical characteristics

Table 6. Thermal & Mechanical characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base			-	1.5	2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[2]	-	-	50	K/W

[2] Surface mount on FR4 board of 1 inch<sup>2</sup>, 1 oz copper.

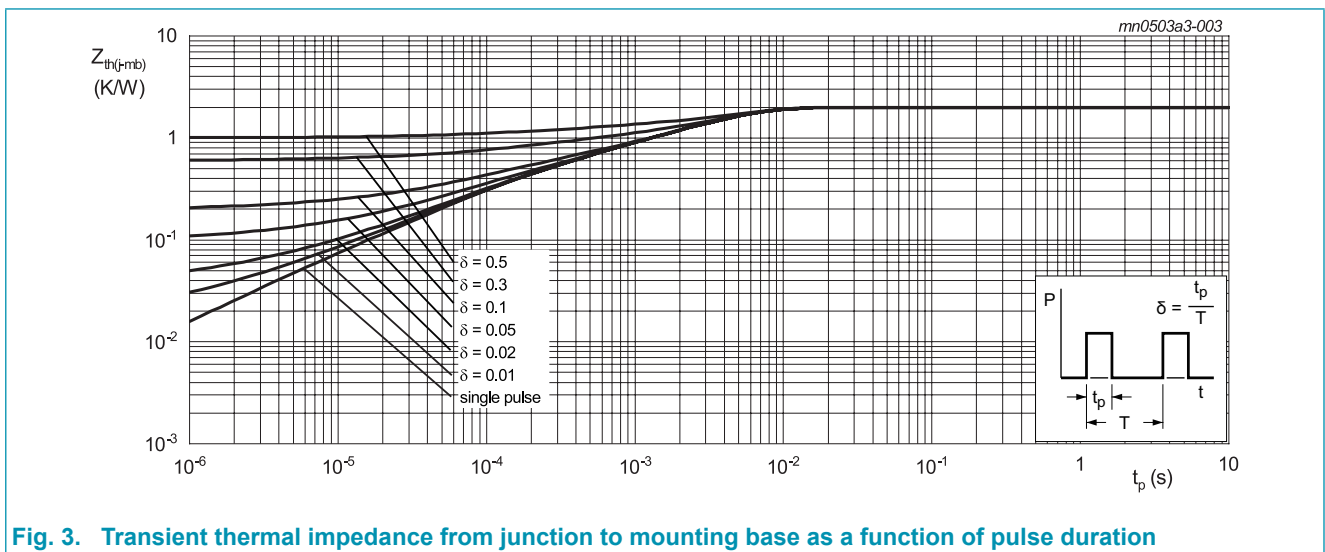


Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

**Table 7. Characteristics**
 $T_j = 25\text{ °C}$  unless otherwise noted

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
<b>Static characteristics</b>							
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\text{ }\mu\text{A}; V_{GS} = 0\text{ V}$		30	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 250\text{ }\mu\text{A}; V_{DS} = V_{GS}$		1.0	1.6	2.4	V
$I_{DSS}$	drain leakage current	$V_{DS} = 30\text{ V}; V_{GS} = 0\text{ V}$		-	-	1	$\mu\text{A}$
		$V_{DS} = 30\text{ V}; V_{GS} = 0\text{ V}; T_j = 125\text{ °C}$		-	-	10	$\mu\text{A}$
$I_{GSS}$	gate leakage current	$V_{GS} = \pm 20\text{ V}; V_{DS} = 0\text{ V}$		-	-	$\pm 100$	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 20\text{ A}$		-	4.1	5.0	m $\Omega$
		$V_{GS} = 4.5\text{ V}; I_D = 20\text{ A}$		-	5.8	8.0	m $\Omega$
$R_G$	gate resistance	$f = 1\text{ MHz}$		-	2.5	-	$\Omega$
<b>Dynamic characteristics</b>							
$Q_{G(tot)}$	total gate charge	$I_D = 20\text{ A}; V_{DS} = 15\text{ V}; V_{GS} = 10\text{ V}$		-	44	-	nC
$Q_{GS}$	gate-source charge			-	7.2	-	nC
$Q_{GD}$	gate-drain charge			-	7.8	-	nC
$C_{iss}$	input capacitance	$V_{DS} = 15\text{ V}; V_{GS} = 0\text{ V}; f = 1\text{ MHz}$		-	2433	-	pF
$C_{oss}$	output capacitance			-	272	-	pF
$C_{rss}$	reverse transfer capacitance			-	217	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 15\text{ V}; V_{GS} = 10\text{ V}; R_G = 6\text{ }\Omega;$ $I_D = 20\text{ A}$		-	7.0	-	ns
$t_r$	rise time			-	22	-	ns
$t_{d(off)}$	turn-off delay time			-	32	-	ns
$t_f$	fall time			-	25	-	ns
<b>Source-drain diode</b>							
$V_{SD}$	source-drain voltage	$V_{GS} = 0\text{ V}; I_S = 1\text{ A}$		-	0.71	1	V
		$V_{GS} = 0\text{ V}; I_S = 1\text{ A}; T_j = 125\text{ °C}$		-	0.54	-	V
$I_S$	body-diode continuous current	$T_{mb} = 25\text{ °C}$		-	-	67	A
$t_{rr}$	reverse recovery time	$V_{GS} = 0\text{ V}; I_S = 20\text{ A}; di/dt = 100\text{ A}/\mu\text{s}$		-	16	-	ns
$Q_{rr}$	reverse recovered charge			-	8.0	-	nC
$I_{rrm}$	reverse recovery current			-	1.0	-	A

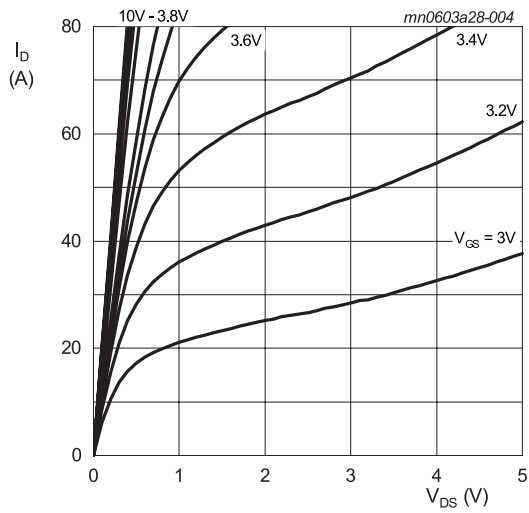


Fig. 4. Drain current as a function of drain-source voltage; typical values

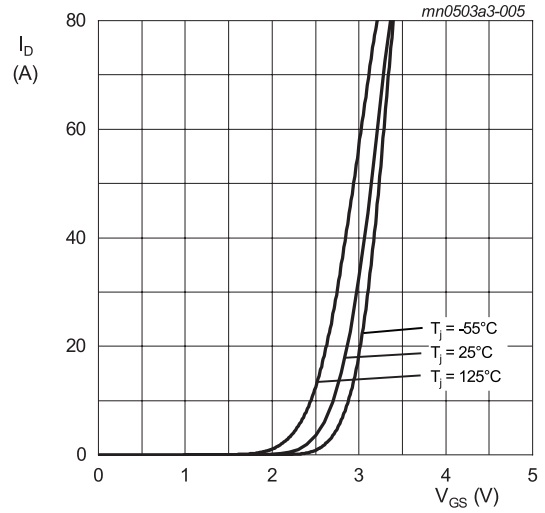


Fig. 5. Drain current as a function of gate-source voltage; typical values  
 $V_{DS} = 5V$

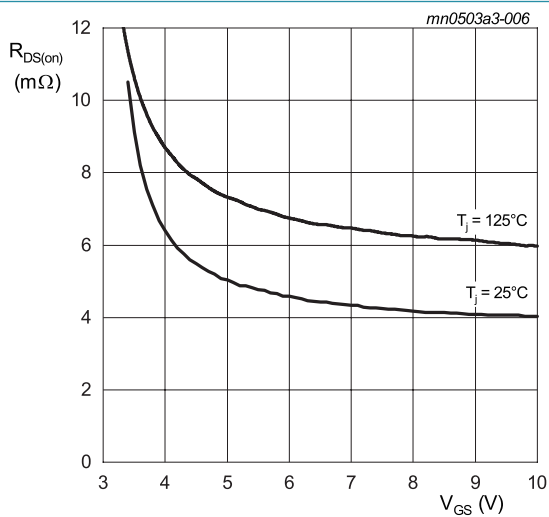


Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values  
 $I_D = 20A$

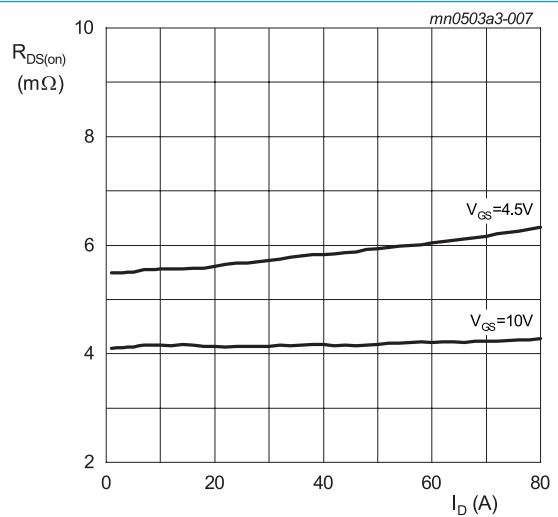
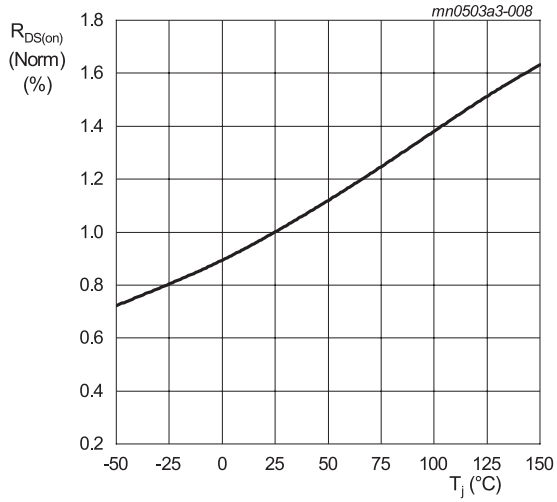
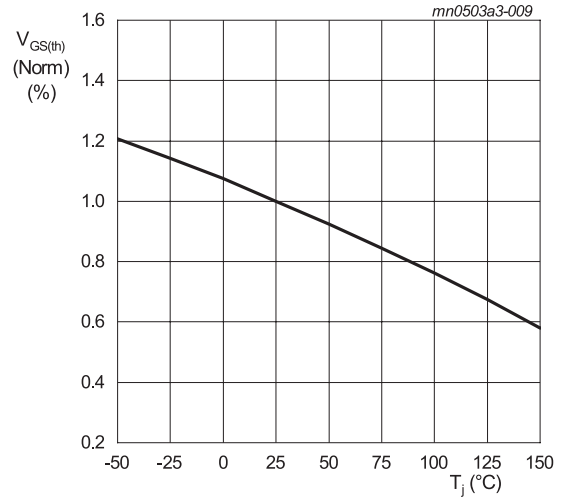


Fig. 7. Drain-source on-state resistance as a function of drain current; typical values



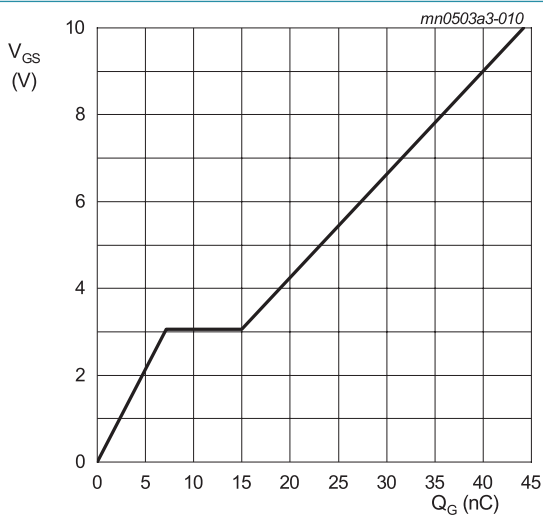
$V_{GS} = 10\text{ V}; I_D = 20\text{ A}$

Fig. 8. Normalized drain-source on-state resistance as a function of junction temperature



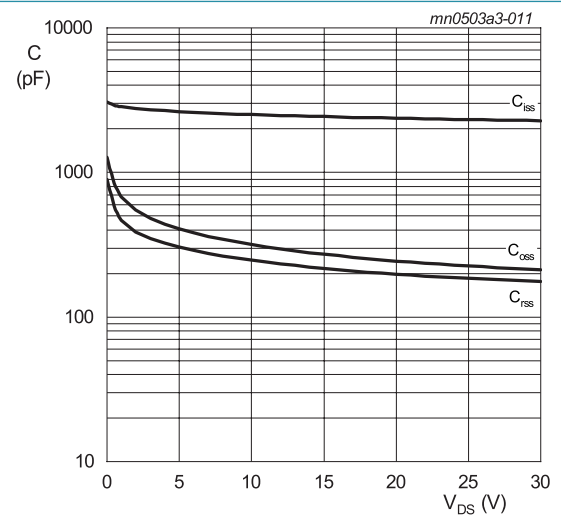
$V_{GS} = V_{GS(th)}; I_D = 250\ \mu\text{A}$

Fig. 9. Normalized gate-source threshold voltage as a function of junction temperature



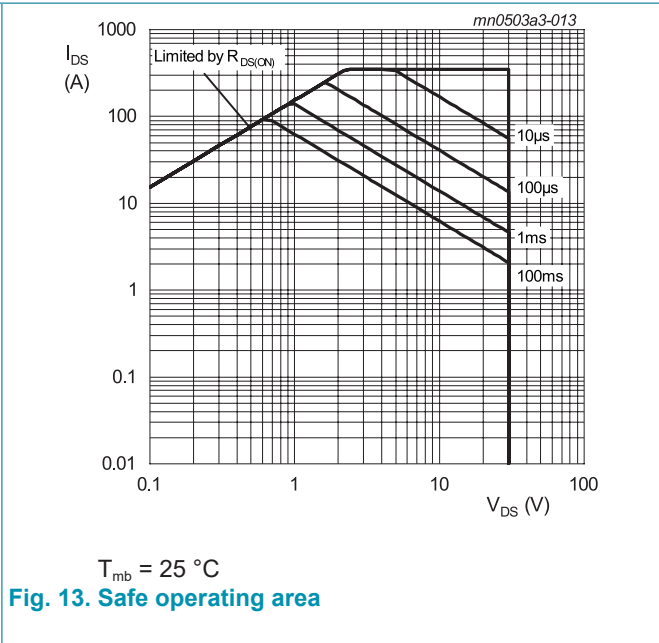
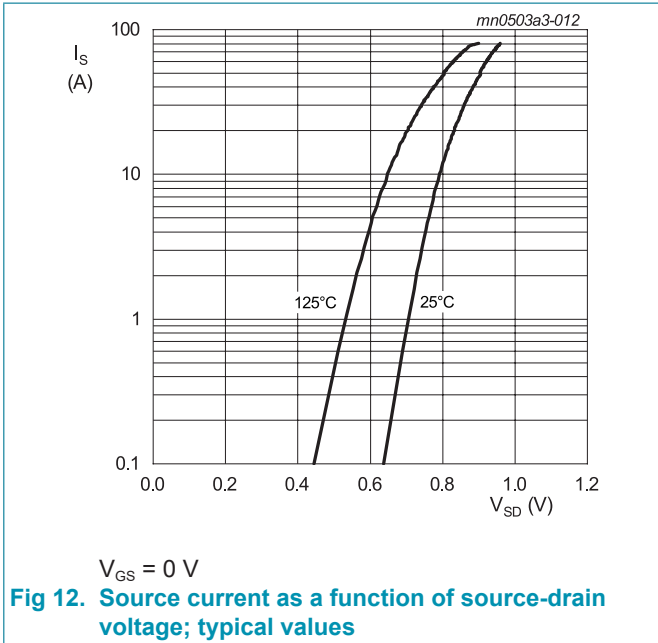
$I_D = 20\text{ A}; V_{DS} = 15\text{ V}$

Fig. 10. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

Fig. 11. Capacitances as a function of drain-source voltage; typical values

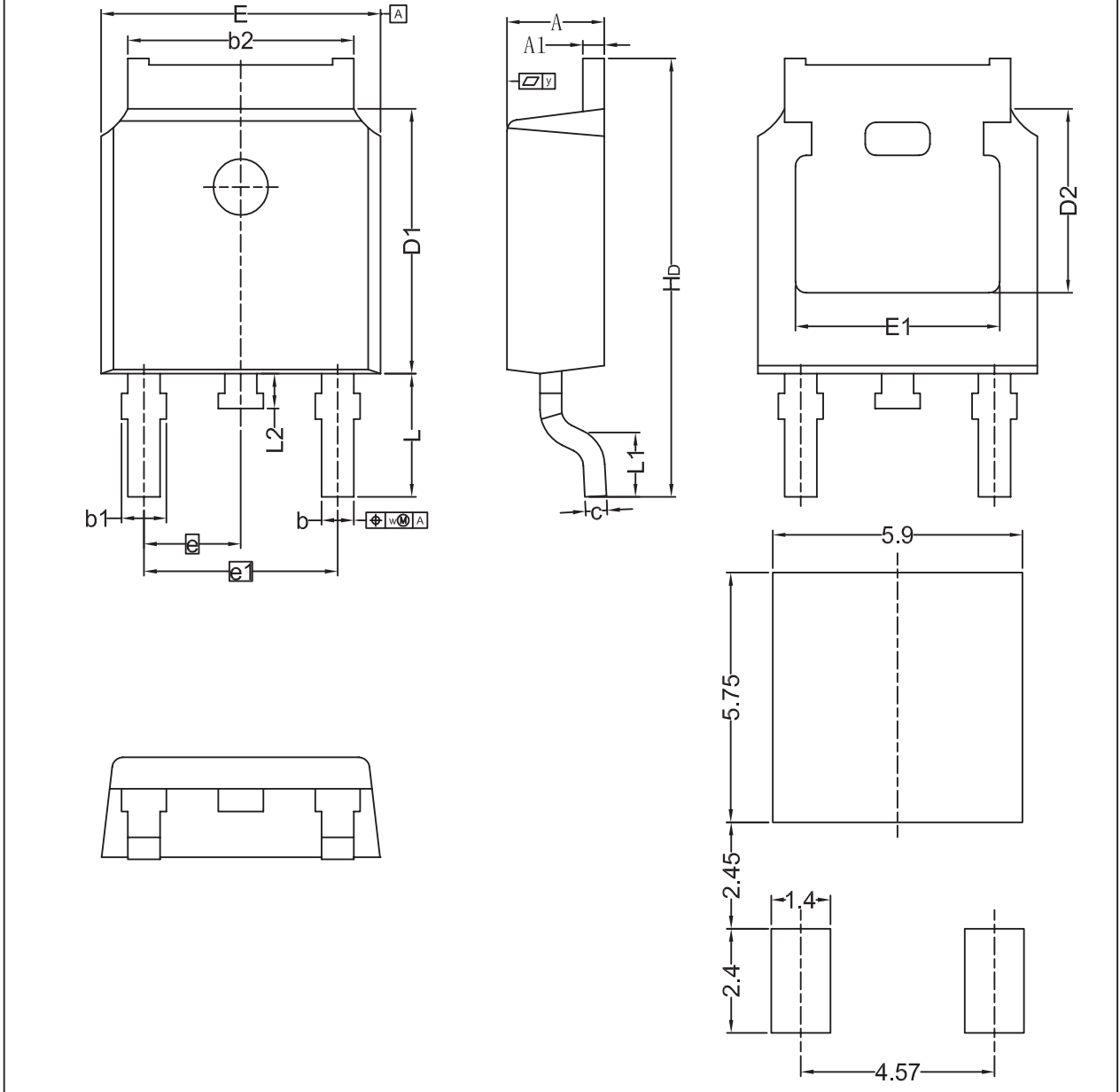




### 11. Package outline

Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)

TO252



Recommended Footprint

Unit	A	A1	b	b1	b2	c	D1	D2	E	E1	e	e1	H <sub>D</sub>	L	L1	L2	w	y
min	2.22	0.46	0.71	0.72	5.00	0.20	5.98	4.00	6.47	4.45	2.285	4.57	9.60	2.90 (Ref.)	0.50	0.50	0.20	0.20
mm nom																		
max	2.38	0.93	0.89	1.10	5.46	0.56	6.22	---	6.73	---			10.40	---	---	0.90		

## 12. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [1] Please consult the most recently issued document before initiating or completing a design.
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